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PMV185XN

30 V, single N-channel Trench MOSFET

3 August 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low R_{DSon}
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	30	V	
V _{GS}	gate-source voltage			-12	-	12	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	1.2	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	185	250	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².





30 V, single N-channel Trench MOSFET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D —
2	S	source		
3	D	drain	1	G 13 24 3 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5 5
				017aaa253

3. Ordering information

Table 3. Ordering information

Type number		Package					
		Name	Description	Version			
	PMV185XN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

4. Marking

Table 4. Marking codes

Table 11 maning course	
Type number	Marking code
	[1]
PMV185XN	EH%

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	1.2	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	1.1	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4.4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	325	mW
			[1]	-	455	mW
		T _{sp} = 25 °C		-	1275	mW

PMV185XN

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	0.7	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

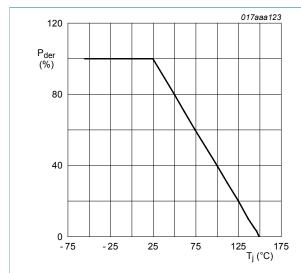


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

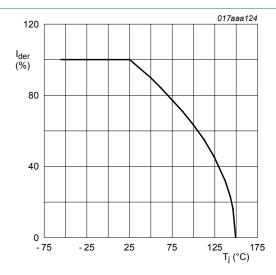


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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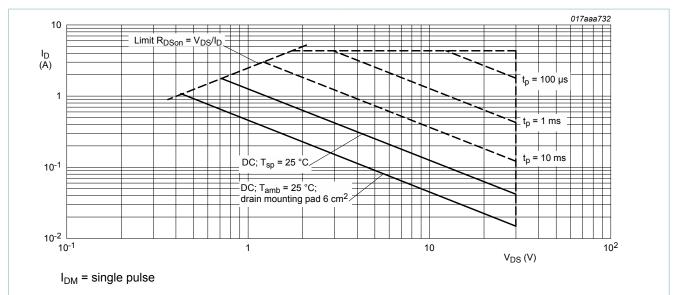


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
(i)(J-a)	thermal resistance		[1]	-	333	385	K/W
	from junction to		[2]	-	240	275	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	203	235	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	85	100	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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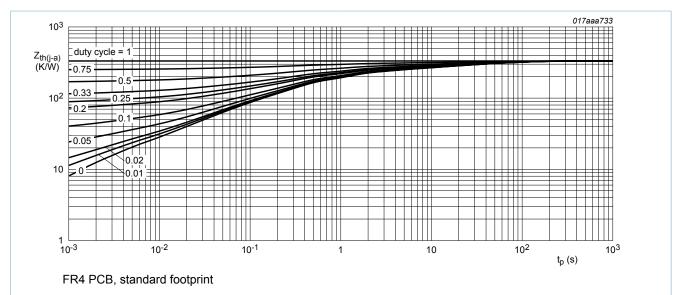


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

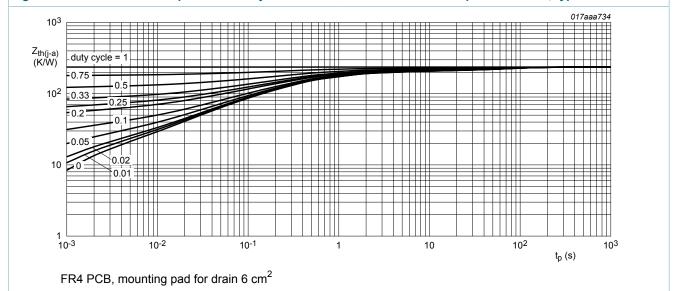


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C		30	-	-	V	
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$		0.5	1	1.5	V	
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _{amb} = 25 °C		-	-	1	μA	
		V _{DS} = 30 V; V _{GS} = 0 V; T _{amb} = 150 °C		-	-	10	μA	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 1.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	185	250	mΩ
	resistance	$V_{GS} = 4.5 \text{ V}; I_D = 1.1 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	300	400	mΩ
		V_{GS} = 2.5 V; I_{D} = 0.25 A; T_{j} = 25 °C	-	255	365	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 1.1 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	2.9	-	S
Dynamic cl	haracteristics		,			
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I_D = 1.1 A; V_{GS} = 4.5 V;	-	0.87	1.3	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.17	-	nC
Q_{GD}	gate-drain charge		-	0.24	-	nC
C _{iss}	input capacitance	V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V;	-	76	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	30	-	pF
C _{rss}	reverse transfer capacitance		-	22	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_{D} = 1.1 A; V_{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	11	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time		-	7	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 0.7 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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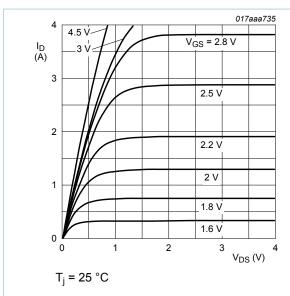
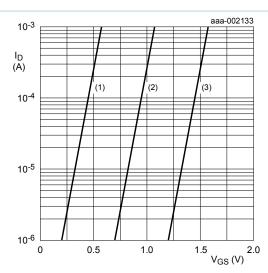


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

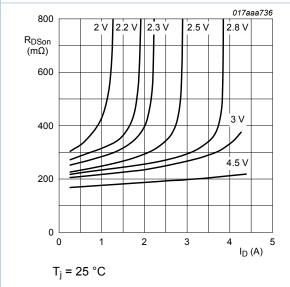


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

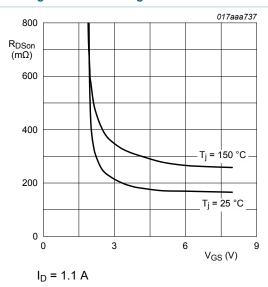


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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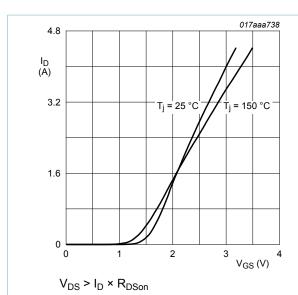


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

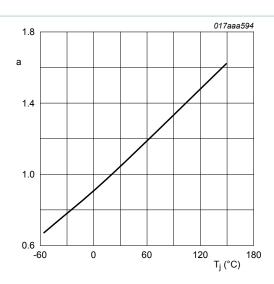


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

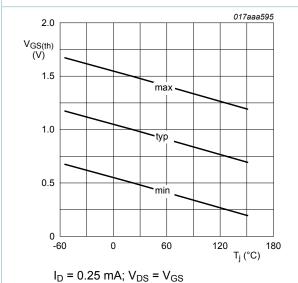


Fig. 12. Gate-source threshold voltage as a function of junction temperature

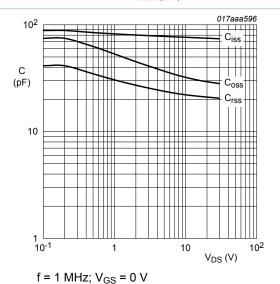
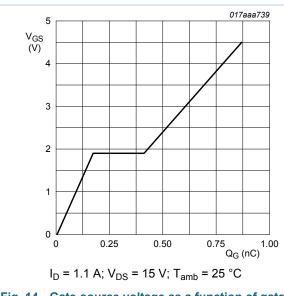


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GG}(tot)
017aaa137

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

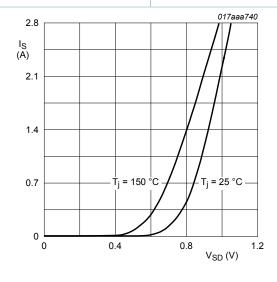
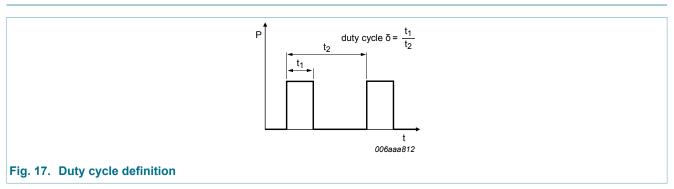


Fig. 16. Source current as a function of source-drain voltage; typical values

8. Test information

 $V_{GS} = 0 V$



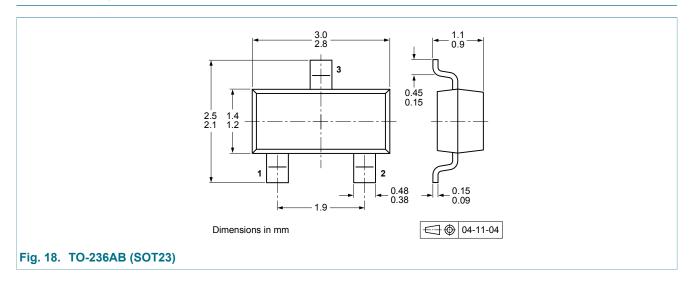
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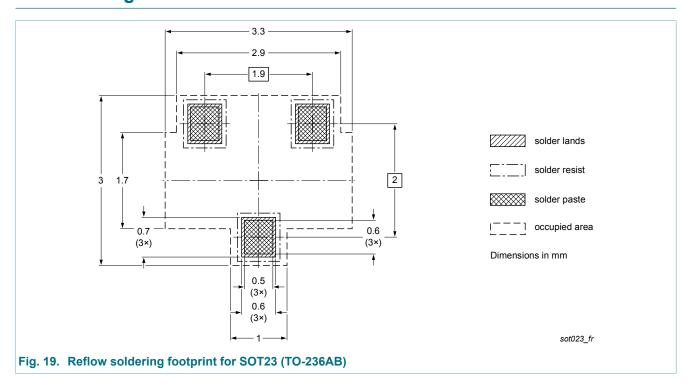
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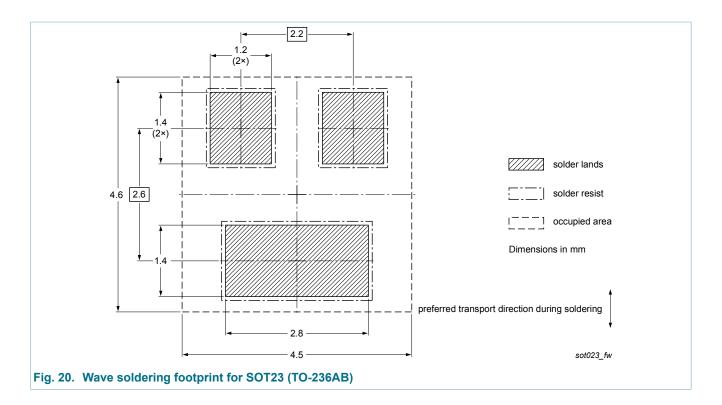
9. Package outline



10. Soldering



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11. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV185XN v.1	20120803	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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